L Number	Hits	Search Text	DB	Time stamp
1	53	("MIS") same ((("C-V") or (CV)) near3	USPAT;	2004/03/18 10:30
*	•	characteristic\$5) same capacit\$5	US-PGPUB;	
		•	EPO; JPO;	
			DERWENT;	
			IBM TDB	
2	1	("6636073").PN.	USPAT;	2004/03/18 10:35
			US-PGPUB	
3	3	(("5107137") or ("5175445") or	USPAT;	2004/03/18 10:36
		("6177826")).PN.	US-PG P UB	
4	1	6636073.pn. and MIS	USPAT;	2004/03/18 10:37
i			US-PGPUB	
5	0	6636073.URPN.	USPAT	2004/03/18 10:38
6	0	6636073.URPN.	USPAT	2004/03/18 10:38
7	0	6636073.URPN.	USPAT	2004/03/18 10:38
8	0	6392623.URPN.	USPAT	2004/03/18 10:40
-	46	(("metal/insulator/semiconductor") or	USPAT;	2004/03/18 10:26
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS")) same ((("C-V") or (CV)) near3	EPO; JPO;	
		characteristic\$5) same capacit\$5	DERWENT;	
			IBM_TDB	2002/12/02 11 46
-	37		USPAT;	2002/12/09 11:46
1		("metal-insulator-semiconductor")or ("MIS")) and ("LCR" adj meter)	US-PGPUB; EPO; JPO;	
		("MIS")) and ("LCR" adj meter)	DERWENT;	
			IBM TDB	
_	1	"4083254".PN.	USPAT;	2002/12/09 11:50
-	1	1003231 .LN.	US-PGPUB	1 2002,12,05 11.50
1_	1	"4322979".PN.	USPAT;	2002/12/09 11:50
	-	1322373 1211.	US-PGPUB	2002, 12, 03
_	1	"4681451".PN.	USPAT;	2002/12/09 11:50
	_		US-PGPUB	
_	72	(("metal/insulator/semiconductor") or	USPAT;	2002/12/09 14:03
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS")) same ((("C-V") or (CV) or	EPO; JPO;	
		(capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or	IBM_TDB	1
		(capacit\$4/voltage)) near3		
		characteristic\$5) same capacit\$5		
-	3	5701088.bi,uref.	USPAT;	2002/12/09 13:37
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
	4	"6177826"	USPAT;	2002/12/09 12:34
-	-	0177020	US-PGPUB;	2002/12/03 12.34
			EPO; JPO;	
			DERWENT;	
1			IBM TDB	
1 -	23	"5175445"	USPAT;	2002/12/09 12:35
			US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
1 -	3	(USPAT;	2002/12/09 12:35
]		("5107137")).PN.	US-PGPUB	
1 -	14	5233291.bi,uref.	USPAT;	2002/12/09 14:00
			US-PGPUB;	
]			EPO; JPO;	
			DERWENT;	
	_	500000	IBM_TDB	2002/12/12 12 22
-	2	5233291.pn.	USPAT;	2002/12/10 10:03
		·	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
<u> </u>	1	"5065103".PN.	USPAT;	2002/12/09 14:00
-		JUUJIUJ .FM.	US-PGPUB	2002/12/03 14:00
1_	1	"4992728".PN.	USPAT;	2002/12/09 14:01
	· •	1555120	US-PGPUB	
	<u> </u>		1 33 13102	<u> </u>

			· · · · · · · · · · · · · · · · · · ·	
-	1	"4941753".PN.	USPAT; US-PGPUB	2002/12/09 14:01
-	1	"4891584".PN.	USPAT; US-PGPUB	2002/12/09 14:01
-	154	<pre>(("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS")) same (("C-V") or (CV) or (capacit\$4 adj voltage) or (capacit\$4-voltage) or (capacit\$4/voltage)) and characteristic\$5</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 14:05
-	155	<pre>and capacit\$5 (("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit\$4 adj voltage) or (capacit\$4-voltage) or</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:12
-	12	<pre>("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit\$4 adj voltage) or (capacit\$4-voltage) or</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 14:35
-	53	<pre>(capacit\$4/voltage)) and characteristic\$5 and capacit\$5) and synthesis ((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor") or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit\$4 adj voltage) or (capacit\$4-voltage) or (capacit\$4/voltage)) and characteristic\$5</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 14:43
-	1	and capacit\$5) and "nm"	USPAT; US-PGPUB; EPO; JPO;	2002/12/09 15:29
-	2	5233292.pn.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/12/09 15:30
-	2	5233291.pn.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/12/09 15:43
_	0	("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit\$4 adj voltage) or (capacit\$4-voltage) or (capacit\$4/voltage)) and characteristic\$5 and capacit\$5) and (("4083254".PN. or	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 15:44
-	9	three) adj nm)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/12/10 07:14
-	1	5233291.pn. and MIS	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/12/10 07:27
-	6860	motohiro.in.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/12/10 07:27
1	1		IBM TDB	1

	6000		USPAT;	2002/12/10 07:28
_	6828	motohiro.inv.	USPAT; US-PGPUB;	2002/12/10 07:28
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	6	motohiro.inv. and ("MAIS")	USPAT;	2002/12/10 07:50
-	"	moconito.inv. and (PAIS)	US-PGPUB;	2002, 12, 10 01.50
			EPO; JPO;	1
!		,	DERWENT;	
	1		IBM TDB	
1_	6	motohiro.inv. and ("MAIS")	USPAT;	2002/12/10 07:50
		motoritio.inv. and (raits)	US-PGPUB;	2002, 12, 10 01100
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	5233291.pn. and synthesis	USPAT;	2002/12/10 10:08
]	"	000003117 4 53	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1	1		IBM TDB	
_	n	5233291.pn. and switch\$5	USPAT;	2002/12/10 10:11
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	5233291.pn. and select\$5	USPAT;	2002/12/10 10:12
1		•	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	155	(("metal/insulator/semiconductor") or	USPAT;	2002/12/10 10:13
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or	IBM_TDB	
		(capacit\$4/voltage)) and characteristic\$5		
		and capacit\$5		0000/10/10 10 15
-	107		USPAT;	2002/12/10 10:15
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO; DERWENT;	
		or (capacit\$4 adj voltage) or	1	
		(capacit\$4-voltage) or	IBM_TDB	
		(capacit\$4/voltage)) and characteristic\$5 and capacit\$5) and (switch\$5 or select\$5)		
_	54		USPAT;	2002/12/10 10:28
1 -	54	("metal-insulator-semiconductor") or	US-PGPUB;	2302, 12, 10 10.20
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
	1	(capacit \$4 - voltage) or	IBM TDB	
	1.	(capacit\$4/voltage)) and characteristic\$5		
1		and capacit\$5) and ((switch\$5 or		
		select\$5) same (capacit\$5))		
_	122		USPAT;	2002/12/10 10:30
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or	IBM_TDB	,
		(capacit\$4/voltage)) and characteristic\$5	-	
		and capacit\$5) and ((switch\$5 or select\$5		
1	ì	or elect\$5) same (capacit\$5))	1	

_	68	<pre>(((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor") or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit\$4 adj voltage) or (capacit\$4-voltage) or (capacit\$4/voltage)) and characteristic\$5 and capacit\$5) and ((switch\$5 or select\$5 or elect\$5) same (capacit\$5))) not (((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor") or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit\$4 adj voltage) or (capacit\$4-voltage) or (capacit\$4/voltage)) and characteristic\$5</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:54
-	31	<pre>and capacit\$5) and ((switch\$5 or select\$5) same (capacit\$5))) ((silicon adj oxide) near2 thickness) near2 (("3" or three) adj "nm")</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/12/10 10:57
-	13	(((silicon adj oxide) near2 thickness) near2 (("3" or three) adj "nm")) and @ad<20001212	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/12/10 11:15
_	6	((((silicon adj oxide) near2 thickness) near2 (("3" or three) adj "nm")) and @ad<20001212) and capacit\$5	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/12/10 11:24
_	2	jp-11150246-\$.did.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/12/10 12:46
_	1	("5233291").PN.	IBM_TDB USPAT;	2002/12/10 13:07
_	1	("4510516").PN.	US-PGPUB USPAT;	2002/12/10 13:10
_	1	("5568252").PN.	US-PGPUB USPAT;	2002/12/10 13:14
_	1	("5266892").PN.	US-PGPUB USPAT;	2002/12/10 13:16
_	1	("5360989").PN.	US-PGPUB USPAT;	2002/12/10 13:17
_	1	("3646527").PN.	US-PGPUB USPAT;	2002/12/10 13:17
-	2 0	(("5654588") or ("5973504")).PN. 5654588.pn. and (silicon near3 oxide)	US-PGPUB USPAT; USPAT; US-PGPUB; EPO; JPO;	2004/02/17 14:44 2004/02/18 14:52
_	0	5654588.pn. and (silicon near3 thickness)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/18 14:52
-	0	5654588.pn. and (silicon same thickness)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/18 14:52
-	1	5654588.pn. and (thickness)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/18 14:52
			IBM_TDB	